# BC808-25LT1G, BC808-40LT1G

# **General Purpose Transistors**

### **PNP Silicon**

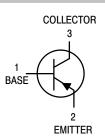
#### **Features**

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

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SOT-23 CASE 318 STYLE 6

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	$V_{CEO}$	-25	V
Collector - Base Voltage	V <sub>CBO</sub>	-30	V
Emitter - Base Voltage	V <sub>EBO</sub>	-5.0	V
Collector Current – Continuous	Ic	-500	mAdc

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.
- 2. Alumina = 0.4 x 0.3 x 0.024 in 99.5% alumina.

#### **MARKING DIAGRAM**



5x = Device Code x = F or G M = Date Code\*

■ = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

# BC808-25LT1G, BC808-40LT1G

## **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted.)

Characteristic	_	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS		•	•	•		
Collector – Emitter Breakdown Voltage (I <sub>C</sub> = –10 mA)		V <sub>(BR)CEO</sub>	-25	_	-	V
Collector – Emitter Breakdown Voltage (V <sub>EB</sub> = 0, I <sub>C</sub> = –10 μA)		V <sub>(BR)CES</sub>	-30	_	-	V
Emitter – Base Breakdown Voltage ( $I_E = -1.0 \mu A$ )		V <sub>(BR)EBO</sub>	-5.0	-	-	V
Collector Cutoff Current $(V_{CB} = -20 \text{ V})$ $(V_{CB} = -20 \text{ V}, T_J = 150^{\circ}\text{C})$		I <sub>CBO</sub>	- -	- -	-100 -5.0	nA μA
ON CHARACTERISTICS				•		
DC Current Gain $(I_C = -100 \text{ mA}, V_{CE} = -1.0 \text{ V})$ $(I_C = -500 \text{ mA}, V_{CE} = -1.0 \text{ V})$	BC808-25LT1G BC808-40LT1G	h <sub>FE</sub>	160 250 40	- - -	400 600 –	-
Collector – Emitter Saturation Voltage (I <sub>C</sub> = -500 mA, I <sub>B</sub> = -50 mA)		V <sub>CE(sat)</sub>	_	=	-0.7	V
Base – Emitter On Voltage (I <sub>C</sub> = -500 mA, I <sub>B</sub> = -1.0 V)		V <sub>BE(on)</sub>	-	-	-1.2	V
SMALL-SIGNAL CHARACTERISTICS				•		
Current – Gain – Bandwidth Product (I <sub>C</sub> = –10 mA, V <sub>CE</sub> = –5.0 Vdc, f = 100 MHz)		f <sub>T</sub>	100	_	_	MHz
Output Capacitance (V <sub>CB</sub> = -10 V, f = 1.0 MHz)		C <sub>obo</sub>	_	10	-	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

#### **ORDERING INFORMATION**

Device	Specific Marking	Package	Shipping <sup>†</sup>
BC808-25LT1G	5F	SOT-23	2000 / Tana & Baal
SBC808-25LT1G	ЭF	(Pb-Free)	3000 / Tape & Reel
BC808-40LT1G	5G	SOT-23 (Pb-Free)	3000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## BC808-25LT1G, BC808-40LT1G

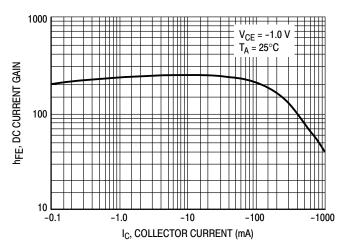


Figure 1. DC Current Gain

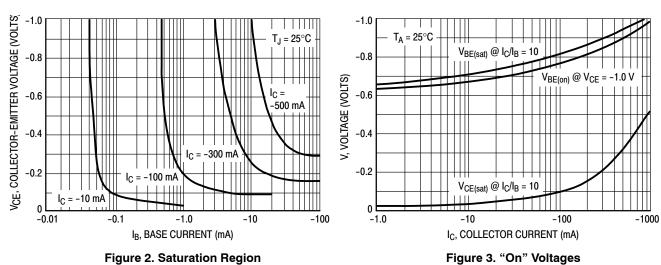


Figure 2. Saturation Region

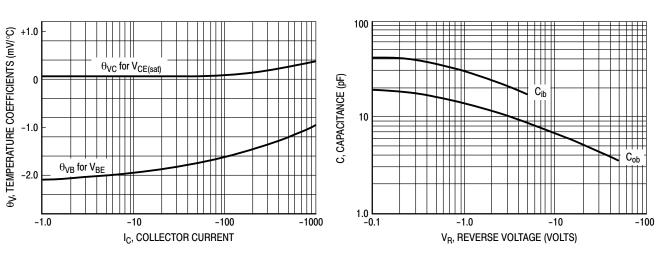


Figure 4. Temperature Coefficients

Figure 5. Capacitances



SOT-23 (TO-236) CASE 318-08 **ISSUE AS** 

**DATE 30 JAN 2018** 

# SCALE 4:1 D - 3X b

**TOP VIEW** 







#### **RECOMMENDED SOLDERING FOOTPRINT**



DIMENSIONS: MILLIMETERS

#### NOTES:

- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETERS.
  3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
  MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,

	PROT	RUSIONS, OR GATE BURRS.	
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	MILLIMETERS				INCHES	
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0°		10°	0°		10°

#### **GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code

= Date Code

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE
OT (1 F O			

SOT-23 (TO-236)

STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
<ol><li>ANODE</li></ol>	<ol><li>SOURCE</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>CATHODE</li></ol>	2. DRAIN	2. GATE
<ol><li>CATHODE</li></ol>	3. GATE	<ol><li>CATHODE-ANODE</li></ol>	<ol><li>ANODE</li></ol>	3. GATE	<ol><li>ANODE</li></ol>

STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	PIN 1. CATHODE	PIN 1. CATHODE
<ol><li>CATHODE</li></ol>	<ol><li>CATHODE</li></ol>	2. ANODE	<ol><li>CATHODE</li></ol>	2. ANODE	<ol><li>ANODE</li></ol>
<ol><li>ANODE</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>ANODE</li></ol>	<ol><li>CATHODE-ANOD</li></ol>	E 3. GATE

STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
<ol><li>SOURCE</li></ol>	<ol><li>OUTPUT</li></ol>	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3 DRAIN	3 INPLIT	3 CATHODE	3. SOURCE	3. GATE	<ol><li>NO CONNECTION</li></ol>

STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE	
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